

## **isc Silicon NPN Power Transistors**

# 2SC4981

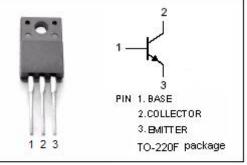
#### DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 80V(Min)
- Low Collector Saturation Voltage
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

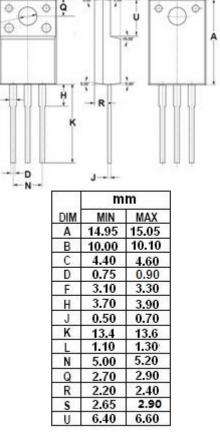
• Designed for use in drivers such as DC/DC converters and actuators.

### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)



SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	100	v
VCEO	Collector-Emitter Voltage	80	v
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	7	А
Ісм	Collector Current-Peak	14	А
Ι <sub>Β</sub>	Base Current-Continuous	1.5	А
I <sub>BM</sub>	Base Current-Peak	2	А
P⊤	Total Power Dissipation @ T <sub>c</sub> =25℃	25	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

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### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case		°C/W

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## INCHANGE SEMICONDUCTOR

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## ELECTRICAL CHARACTERISTICS

#### $T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.1A; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 0.2A			0.3	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 0.2A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	At rated Voltage			100	μA
ICEO	Collector Cutoff Current	At rated Voltage			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	At rated Voltage			100	μA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3.5A ; V <sub>CE</sub> = 2V	70			
fī	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.7A ; V <sub>CE</sub> = 10V		50		MHz

Switching times

t <sub>on</sub>	Turn-on Time			0.3	μ \$
t <sub>stg</sub>	Storage Time	$\begin{array}{l} I_{C}\text{=}~3.5\text{A},~I_{B1}\text{=}~0.35\text{A};~I_{B2}\text{=}~-0.35\text{A};\\ \textbf{R}_{L}\text{=}~8~\Omega~;~\textbf{V}_{BB2}\text{=}~4\text{V} \end{array}$		1.5	μ \$
t <sub>f</sub>	Fall Time			0.2	μS

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